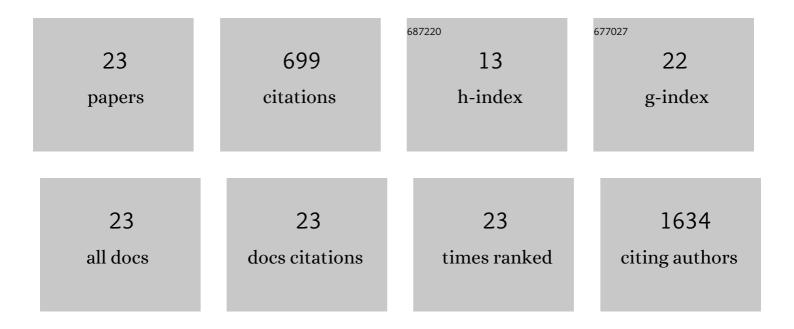
Iddo Amit

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Ultrahigh Performance Nanoengineered Graphene–Concrete Composites for Multifunctional Applications. Advanced Functional Materials, 2018, 28, 1705183. | 7.8 | 161 |
| 2 | High-Mobility and High-Optical Quality Atomically Thin WS 2. Scientific Reports, 2017, 7, 14911. | 1.6 | 77 |
| 3 | Specific and label-free femtomolar biomarker detection with an electrostatically formed nanowire biosensor. NPG Asia Materials, 2013, 5, e41-e41. | 3.8 | 53 |
| 4 | Laser-writable high-k dielectric for van der Waals nanoelectronics. Science Advances, 2019, 5, eaau0906. | 4.7 | 51 |
| 5 | Contact Doping of Silicon Wafers and Nanostructures with Phosphine Oxide Monolayers. ACS Nano, 2012, 6, 10311-10318. | 7.3 | 50 |
| 6 | Role of Charge Traps in the Performance of Atomically Thin Transistors. Advanced Materials, 2017, 29, 1605598. | 11.1 | 46 |
| 7 | Spatially Resolved Correlation of Active and Total Doping Concentrations in VLS Grown Nanowires. Nano Letters, 2013, 13, 2598-2604. | 4.5 | 40 |
| 8 | Strain-engineered inverse charge-funnelling in layered semiconductors. Nature Communications, 2018, 9, 1652. | 5.8 | 36 |
| 9 | Tunable diameter electrostatically formed nanowire for high sensitivity gas sensing. Nano Research, 2015, 8, 2206-2215. | 5.8 | 35 |
| 10 | Barrier Height Measurement of Metal Contacts to Si Nanowires Using Internal Photoemission of Hot Carriers. Nano Letters, 2013, 13, 6183-6188. | 4.5 | 31 |
| 11 | Parallel p–n Junctions across Nanowires by One-Step <i>Ex Situ</i> Doping. ACS Nano, 2014, 8, 8357-8362. | 7.3 | 31 |
| 12 | Sub 20 meV Schottky barriers in metal/MoTe ₂ junctions. 2D Materials, 2018, 5, 025023. | 2.0 | 18 |
| 13 | Multiple State Electrostatically Formed Nanowire Transistors. IEEE Electron Device Letters, 2015, 36, 651-653. | 2.2 | 17 |
| 14 | Density and Energy Distribution of Interface States in the Grain Boundaries of Polysilicon Nanowire. Nano Letters, 2014, 14, 6190-6194. | 4.5 | 14 |
| 15 | Boron Monolayer Doping: Role of Oxide Capping Layer, Molecular Fragmentation, and Doping Uniformity at the Nanoscale. Advanced Materials Interfaces, 2020, 7, 1902198. | 1.9 | 10 |
| 16 | Functionalised hexagonal-domain graphene for position-sensitive photodetectors. Nanotechnology, 2017, 28, 124004. | 1.3 | 9 |
| 17 | Impact of Dopant Compensation on Graded <i>p</i> – <i>n</i> Junctions in Si Nanowires. ACS Applied Materials & Interfaces, 2016, 8, 128-134. | 4.0 | 8 |
| 18 | Potential barrier height at the grain boundaries of a poly-silicon nanowire. Nanotechnology, 2015, 26, 355201. | 1.3 | 4 |

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| # | Article | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Accurate Method To Determine the Mobility of Transition-Metal Dichalcogenides with Incomplete Gate Screening. ACS Applied Materials & amp; Interfaces, 2019, 11, 44406-44412. | 4.0 | 4 |
| 20 | The Effect of Nonideal Polar Monolayers on Molecular Gated Transistors. ACS Applied Materials & Interfaces, 2010, 2, 2289-2292. | 4.0 | 2 |
| 21 | Molecular gating of transistors by amine-terminated layers. Applied Surface Science, 2012, 258, 4069-4072. | 3.1 | 1 |
| 22 | Energy dispersive spectroscopic measurement of charge traps in MoTe2. Physical Review B, 2019, 100, . | 1.1 | 1 |
| 23 | Photo-oxidized HfS2 - An embeddable and writable high-k dielectric for flexible Van der Waals nano-electronics. , 2018, , . | | Ο |
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